NSN 5961-01-262-9098

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-262-9098 **Inclosure Material:** Plastic **Overall Length:** 0.250 inches **Terminal Length:** 0.500 inches **Overall Diameter:** 0.155 inches **Function For Which Designed:** Phototransistor **Internal Configuration:** Point contact **Mounting Method: Terminal Semiconductor Material:** Gallium arsenide sulfide **Voltage Rating In Volts Per Characteristic:** 30.0 collector to emitter voltage, dc and 5.0 emitter to collector voltage, dc **Current Rating Per Characteristic:** 100.00 nanoamperes source cutoff current of standard range **Power Rating Per Characteristic:** 60.0 milliwatts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pn **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0